## A Terraced Scanning Superconducting Quantum Interference Device Susceptom eter with Sub-M icron Pickup Loops

Nicholas C. Koshnick,<sup>1</sup> Martin E. Huber,<sup>2</sup> Julie A. Bert,<sup>1</sup> Cli ord

W.Hicks,<sup>1</sup> Je Large<sup>3</sup>, HalEdwards,<sup>3</sup> and Kathryn A.Moler<sup>1</sup>,

<sup>1</sup>D epartm ents of Physics and Applied Physics, Stanford University, Stanford, CA 94305

<sup>2</sup>Departments of Physics and Electrical Engineering,

University of Colorado Denver, Denver, CO 80217

<sup>3</sup>Circuit Design Repair Lab, Texas Instruments, Dallas, TX 75243

Superconducting Q uantum Interference D evices (SQ U ID s) can have excellent spin sensitivity depending on their magnetic ux noise, pick-up loop diameter, and distance from the sample. We report a family of scanning SQ U ID susceptometers with terraced tips that position the pick-up loops 300 nm from the sample. The 600 nm { 2 m pickup loops, de ned by focused ion beam, are integrated into a 12-layer optical lithography process allowing ux-locked feedback, in situ back-ground subtraction and optimized ux noise. These features enable a sensitivity of 70 electron spins per root Hertz at 4K.

In 1989, Ketchen et al: argued that the advent of sub-micron lithography should enable Superconducting Quantum Interference Devices (SQUIDs) with single electron spin sensitivity. Stationary devices can measure nanom agnets with great success<sup>2</sup>, but it rem ains di cult, even with the highest spin-sensitivity SQ U ID  $\mathrm{s}^3$  , to detect single-molecule eld sources. Scanning devices<sup>4,5,6,7,8,9</sup> make it possible to isolate magnetic eld sources and to perform background measurements in situ<sup>10</sup>. Single-layer scanning nano-SQ U ID s<sup>7</sup> have not yet achieved the excellent ux sensitivity of the best large multi-layer SQUDs. M ultilayer SQUID s thus far have had large pickup areas that do not capture dipole eld lines well thereby lim iting the spin sensitivity of these devices. For a norm aloriented dipole on the center line of a pickup loop of radius R, the spin sensitivity, S<sub>n</sub>, is

$$S_n \left( {}_B = {\stackrel{p}{H}} {\stackrel{T}{z}} \right) = {}_n {\frac{R}{r_e}} {}_1 + {\frac{h^2}{R^2}} {}_2^{3=2}$$
 (1)

where  $_{n}$  is the ux noise in units of  $_{0}^{=}$  Hz, h is the pickup loop's height above the sample, and  $r_{e}$ 

2:82 10 <sup>15</sup> m<sup>1</sup>. On the center line, near-optimal signal is achieved for h < R. The spin sensitivity can be further in proved by placing the dipole near the edge of the pickup loop, although dem agnetization limits this enhancement for h < w, where w is the linewidth. For sim – plicity, we use Eq. 1 to compare representative published scanning SQUIDs (Table 1).

Our scanning SQUID combines Focused Ion Beam (FIB) de ned pick-up loops with a 12 layer optical lithography process that includes local eld coils. Integrated terraces minimize h. We characterize the imaging kernel with a superconducting vortex and a dipole eld source. Flux noise measurements at 4 K elvin demonstrate a spin sensitivity of 70  $_{\rm B} = {\rm Hz}$ . Flux noise may decrease at lower temperatures<sup>9,13</sup> leading to a projected sensitivity of . 15  $_{\rm B} = {\rm Hz}$ .

Our susceptometer incorporates two symmetric counter-wound arms, each with an integrated modulation loop, pickup loop, and local eld coil (Fig 1a). A

TABLE I: Survey of reported scanning SQUID s and estim ated spin sensitivity for h=0~(Eq. 1). W ith one exception<sup>7</sup>, the corners are typically 20-60 m from the pickup loop, likely limiting h to 1 { 3 m. For rectangular loops we use R =  $(l_1\,l_2=~)^{1-2}$ .

Principal	Year	Size	F lux Noise	Spin Sensitivity
Investigator		$(m^2)$	$( _0 = Hz)$	$(_{\rm B} = \overline{\rm Hz})$
Vu <sup>4</sup>	1993	100	3	6,000
K irtley <sup>5</sup>	1995	81	2	3,700
M orooka <sup>6</sup>	2000	$16^{11}$	8	6 <b>,</b> 400 <sup>11</sup>
Hasselbach <sup>7</sup>	2000	4	100	40,000
F reitag <sup>8</sup>	2006	12	2	1,400
Huber <sup>9</sup>	2008	12	0.812	640 <sup>12</sup>
Present Work	2008	0.3	0.7	74

three m etalization layer, linear coaxial transm ission line geometry shields the device from magnetic elds. The transmission line geometry has a low inductance per unit length ( 10 pH/mm), which allows for a large separation between the feedback/junction area and the two pickup loops without signi cantly increasing the devices theoretical white noise  $oot^4$ . The separation perm its the use of standard, well optim ized junction and resistive shunt fabrication processes<sup>15</sup>. The resistive shunts ensure a non-hysteretic response. The scanning SQUID is voltage biased and its current is amplied with a SQUID Series Array (SSA) ampli et<sup>6</sup>. A feedback circuit controls the current in the modulation loop, responding to the SSA output voltage to create a ux locked loop. Feedback linearizes the signal and allows for optim alsensitivity at all applied elds. The counter-wound eld coils aid background subtraction<sup>9</sup>. By applying a local eld to the sam ple only in the area of the pickup loop, the eld coils also allow for a low magnetic eld environment near the junction, modulation, and ampli cation stages.

To achieve optimal ux noise<sup>14</sup>, each junction's criticalcurrent,  $I_0$ , is approximately half the superconducting ux quantum,  $_0=2$ , divided by the SQ U ID's self inductance, L. At 4 K, we have a 0.7  $_{0}^{p}$  Hz noise oor above 300 Hz and 1.2  $_{0}^{p}$  Hz 1/f-like noise at 10 Hz (Fig. 2f). If the dom inant ux noise is Johnson noise in the shunt resistors, as indicated by T<sup>1=2</sup> temperature dependence in a previous sim ilar device<sup>9</sup>, a white noise oor of 0.25  $_{0}^{=}$  Hz may be achievable at 300 m K<sup>13</sup>. Cooling ns attached to the shunt resistors of some devices to m inim ize the e ect of electron-phonon coupling lim ited cooling may enable a white noise oor of 0.12  $_{0}^{=}$  Hz at dilution refrigerator temperatures<sup>13</sup>.

W hen limited by Johnson noise in resistive shunts, the theoretical ux noise dependence scales<sup>14</sup> like L<sup>3=2</sup>, whereas quantum noise scales like L<sup>1=2</sup>. The incentive for a well quanti ed low inductance adds to the criteria for optimal pickup loop design. W hen the width, w, or the thickness, t, of a superconducting feature become smaller than the penetration depth, , kinetic inductance can overcome the geom etrical inductance contribution<sup>17</sup> and scales like L<sub>k</sub> / <sup>2</sup>=wt<sup>18</sup>. Thus, linew idths smaller than are undesirable. This e ect, along with phase winding

considerations related to coherence length  $e = ects^9$ , ultimately sets the pickup loop size limit. Inductance also scales with feature length, so we have kept the sub-micron portion of the leads short, just long enough to allow the pickup loop to touch down inst without excessive stray pickup.

For optimal coupling, a dipole on the center line of the pickup loop should have h < R, while a dipole near the edge of the pickup loop should have h < w. Fig. 1b shows a optically de ned, w = 0.6 m, R = 3.2 m, pickup loop pattern with etch features inside and outside the eld coil. The outer etch supplem ents hand polishing to bring the corner of the chip close to the eld coil, and the inner etch reduces the oxide layer above the eld coil. The thickness of the multiple layers are in portant parts of the design. In Fig. 1b, the pickup loop is under 250 nm of SiO<sub>2</sub> as required for a top layer of shielding<sup>13</sup>. It is thus at least this distance from the surface. The well created by the circular eld coil allows little tolerance from the optim al alignm ent angle of 2.5 degrees (Inset Fig. 1b). Additionally, it is di cult to align the device such that the o -center eld coil leads don't touch down rst. W hile the SiO<sub>2</sub> layer and lim ited alignment tolerance is suitable for the w and R of the optically patterned design, these e ects are detrim ental for sub-m icron pickup bops.

W e explored several techniques to create superconducting sub-m icron pickup loops integrated with the multilayer structure: ebeam de ned lift-o lithography with Al, ebeam lithography for etching optically patterned Nb layers, and FIB etching of optically patterned Nb layers. The FIB etching was the most tractable. We also found that sputtered Nb has a sm aller penetration depth (90 nm) than e-beam evaporated Alpatterned with PMMA lifto (120-160 nm), allowing for sm aller linewidths and reducing the calculated<sup>20</sup> inductance for a pair of pickup loops (22 pH vs. 66 pH). The inductance of the rest of the design is 60-65 pH. Here, we only report results from



FIG.1: a) D iagram of a counterwound SQUID susceptom eter. Both the optically patterned tips (b) and FIB de ned tips (c, d) feature etch de ned terraces that reduce the pickup loop to sample distance. Figure b, inset: AFM data down the center line of the device showing that the pickup loop is closest to the surface when the tip is aligned at precisely 2.5 degrees (m ore detail in<sup>13</sup>). In the FIB design (c), the thickness of the eld coil and and pickup loop leads combine with the inner terrace to form a high centerline that allows roll angle tolerance. Figure c, inset: AFM data showing the pickup loop can touch down rst when the pitch angle is between 2 -5. Pickup loops down to 600 nm can be reliably fabricated with a FIB de ned etch process of the topm ost layer.

optically and FIB de ned Nb tips.

O ur F IB design uses three superconducting layers (F ig 1c) such that the eld coil lines (gray) run underneath a shielding layer (purple) and approach the tip from the same angle as the pickup loop. The pickup loop on the top layer (green) is closest to the sample, which also allows for post-optical F IB processing. This design allows the pickup loop to touch rst when the SQ U ID is aligned to a pitch angle of 2 { 5 (F ig. 1c inset), with a roll tolerance equal to the pitch angle.

To increase durability, we fabricated som e devices with the pickup loop retracted from the end of the etch-de ned  $SiD_2$  tab (F ig 1d), allowing the  $SiD_2$  to take the brunt of the wear. The  $SiD_2$  tab also overlaps with the inside edge of the eld coil, making a high point that protects the pickup loop for pitch angles less than 2 degrees. The alignment angle is di cult to set accurately and can change due to therm al contractions, so these considerations are important for protecting the device.

We imaged  $Sr_2RuO_4$  (Fig. 2) to characterize the FIB-de ned device's coupling to a sample. Flux from a monopole-like superconducting vortex can couple through both the pickup loop and its leads (Fig. 2a). Our sm allest SQUID s are designed to do comparative studies on and o a particular mesoscopic structure, rather than



FIG.2: a) A FIB-fabricated device's magnetom etry response near an isolated superconducting vortex. Both positive and negative ux coupling occurs near the leads to the pickup loop (shown on the right side). (b-f) data and modeled results for a pickup loop with a 500 nm inner diam eter and 250 nm linewidth. The ux captured from an isolated surface dipole (b) and monopole magnetic eld source (c) agrees with the modeled results (d,e) calculated by integrating the eld lines that thread a pickup loop kernal located 400 nm above the surface. (f) Linescans of (b-e) o set for clarity. (g) Noise spectrum at 4 K. The green dots show averaged values and the black line displays the average between 2 K H z and 5 K H z

E lectronic address: km oler@ stanford.edu

- <sup>1</sup> M.Ketchen, D.Awschalom, W.Gallagher, A.Kleinsasser, R.Sandstrom, J.Rozen, and B.Bumble, Magnetics, IEEE Transactions on 25, 1212 (1989).
- <sup>2</sup> W. Wernsdorffer, E. B. Orozco, K. Hasselbach, A. Benoit, B. Barbara, N. Demoncy, A. Loiseau, H. Pascard, and D. Mailly, Physical Review Letters 78, 1791 (1997), and related re erences.
- <sup>3</sup> J.P.Cleuziou, W.Wemsdorfer, V.Bouchiat, T.Ondarcuhu, and M.Monthioux, Nat Nano 1, 53 (2006).
- <sup>4</sup> L.Vu and D.V.Harlingen, Applied Superconductivity, IEEE Transactions on 3, 1918 (1993).
- <sup>5</sup> J.R.Kirtley, M.B.Ketchen, K.G.Stawiasz, J.Z.Sun, W.J.Gallagher, S.H.Blanton, and S.J.W ind, Applied Physics Letters 66, 1138 (1995).
- <sup>6</sup> T.Morooka, K.Tanaka, A.O dawara, S.N akayama, A.Nagata, M. Ikeda, and K.Chinone, Phys.C 335, 157 (2000).
- <sup>7</sup> K.Hasselbach, C.Veauvy, and D.Mailly, Physica C 332, 140 (2000).
- <sup>8</sup> M. Freitag, J. Tsang, J. Kirtley, A. Carlsen, J. Chen, A. Troem an, H. Hilgenkam p, and P. Avouris, Nano Letters 6, 1425 (2006).
- <sup>9</sup> M.E.Huber, N.C.Koshnick, H.Bluhm, L.J.Archuleta, T.Azua, P.G.Bjornsson, B.W.Gardner, S.T.Halloran, E.A.Lucero, and K.A.Moler, Review of Scientic

provide a point like in aging kernel.

Fitting a simple model of the pickup loop response to the vortex and dipole (Fig. 2b-g) gives an elective h. The vortex model is a monopole eld source one penetration depth ( $_{Sr_2Ru0_4} = 150 \text{ nm}$ ) below the surface<sup>5</sup>. The dipole model is a free-space dipole eld source at the surface. The eld from each of these two sources is integrated over the elective pickup loop area at an elective height h<sub>eff</sub> = 400 nm. This h<sub>eff</sub> in plies that the closest side of the 200 nm thick pickup loop is 300 nm above the scanned surface. Several elects could make this estimate of h larger than the physical distance from the sample, such as the existence of a M eissner im age dipole,  $_{Sr_2Ru0_4} > 150 \text{ nm}$  due to dead layers or nite T, and dem agnetization elects from the thickness of the pickup loop.

In <u>ponclusion</u>, we have demonstrated SQUID swith 0.7  $_0 = Hz$  ux noise at 4 K, reliable FIB pickup loops with diameters as small as 600 nm, and a terraced geom – etry that allow sthe pickup loop to come within 300 nm of the <u>surface</u>. These features give a spin sensitivity of 70  $_{\rm B} = Hz$ , that is, the device noise is equivalent to the signal from a single electron spin after an averaging time of a little more than one hour. At lower tem peratures a lower ux noise is likely, leading to spin sensitivities less than 15  $_{\rm B} = Hz$ .

We acknowledge funding from NSF grants PHY-0425897, DMR-0507931, and ECS-9731293 and would like to thank Hendrik Bluhm and John Kirtley for helpful discussions.

Instrum ents 79, 053704 (2008).

- <sup>10</sup> N.C.Koshnick, H.Bluhm, M.E.Huber, and K.A.Moler, Science 318, 1440 (2007).
- <sup>11</sup> Calculations from relevant line m idpoints.
- $^{\rm 12}$  F lux noise at 4.2 K .
- $^{\rm 13}$  Supplem entary Online M aterial.
- <sup>14</sup> C.D. Tesche and J.C larke, Journal of Low Temperature Physics 29, 301 (1977).
- <sup>15</sup> J.Sauvageau, C.Burroughs, P.Booi, M.Cromar, R.Benz, and J.Koch, Applied Superconductivity, IEEE Transactions on 5, 2303 (1995).
- <sup>16</sup> M.E.Huber, P.A.Neil, R.G.Benson, D.A.Bums, A.F. Corey, C.S.Flynn, Y.K itaygorodskaya, O.M assihzadeh, J.M.M artinis, and G.C.Hilton, Applied Superconductivity, IEEE Transactions on 11, 4048 (2001).
- <sup>17</sup> E. H. Brandt and J. R. Clem, Physical Review B 69, 184509 (2004).
- <sup>18</sup> J. B. Majer, J. R. Butcher, and J. E. Mooij, Applied Physics Letters 80, 3638 (2002).
- <sup>19</sup> K. Hasselbach, D. M ailly, and J. R. Kirtley, Journal of Applied Physics 91, 4432 (2002).
- <sup>20</sup> M.Kamon, M.Tsuk, and J.W hite, Microwave Theory and Techniques, IEEE Transactions on 42, 1750 (1994).